

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning at page 9, line 21, with the following rewritten paragraph:

--In Figure 1, an interconnection 11 is constituted by a metal layer 39, which is formed on an insulating film 10 formed on a semiconductor substrate ~~(not shown)~~ 1 on which a device element or an interconnection is formed. Carbon nanotubes 14 are mixed in the metal layer 39 which constitutes the interconnection 11. The carbon nanotube 14 is formed on a particle 15 of nickel formed on the insulating film 10. The particle 15 acts as a catalyst during the growth of the carbon nanotube, and the carbon nanotube 14 grows, with the particle 15 serving as a nucleus.—

Please replace the paragraph beginning at page 10, line 6, with the following rewritten paragraph:

--The insulating film 10 is formed on a silicon substrate ~~(not shown)~~ 1 on which a semiconductor device element is formed.—

Please replace the paragraph beginning at page 12, line 25, with the following rewritten paragraph:

--The interconnection structure by the single damascene process will be described. There are formed an insulating film 10, which is formed on a semiconductor substrate ~~(not shown)~~ 1 on which a device element or an interconnection is formed, an interlayer dielectric film 12 formed on the insulating film 10, and an etching stopper layer 16.—

Please replace the paragraph beginning at page 13, line 16, with the following rewritten paragraph:

--The insulating film 10, the interlayer dielectric film 12 formed on the insulating film 10, and the etching stopper layer 16 formed from SiC (film thickness 30 nm) by the plasma CVD method on the interlayer dielectric film 12 are formed on a silicon substrate ~~(not shown)~~ 1 on which a semiconductor device element is formed. The etching stopper film 16 works also as a diffusion preventing film that prevents a metal which becomes an interconnection from diffusing into the insulating film.--

Please replace the paragraph beginning at page 17, line 17, with the following rewritten paragraph:

--The insulating film 10 formed on a silicon substrate ~~(not shown)~~ 1 on which a semiconductor device element is formed, the interlayer dielectric film 12 formed on the insulating film 10, and the interconnection 11 formed in a trench portion, which is formed in the interlayer dielectric film 12 formed on the insulating film 10 and this first interlayer dielectric film 12 are formed from the barrier metal layer 13 and a metal. The etching stopper layers 16 and 27 are formed on the interlayer dielectric film 12. The interlayer dielectric film 29 and the etching stopper layer 30 are formed on the etching stopper layer 16 (Figure 6 (a)).--

Please replace the paragraph beginning at page 19, line 14, with the following rewritten paragraph:

--This embodiment provides, on an insulating film 10 formed on a substrate ~~(not shown)~~ 1 including a semiconductor device element, the first interconnection layer 59, a connection plug 60 and a second interconnection layer 61. The first interconnection layer 59 is constituted by the interlayer dielectric layer 12, the interconnection 11, the barrier metal layer 13, and the etching stopper layers 16 and 47.--